

CD74HC393, CD74HCT393

High Speed CMOS Logic Dual 4 -Stage Binary Counter

Features

- Fully Static Operation
- Buffered Inputs
- Common Reset
- Negative-Edge Clocking
- Typical $f_{MAX} = 60$ MHz at $V_{CC} = 5V$, $C_L = 15pF$, $T_A = 25^\circ C$
- Fanout (Over Temperature Range)
 - Standard Outputs 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range . . . $-55^\circ C$ to $125^\circ C$
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: $N_{IL} = 30\%$, $N_{IH} = 30\%$ of V_{CC} at

$V_{CC} = 5V$

- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility, $V_{IL} = 0.8V$ (Max), $V_{IH} = 2V$ (Min)
 - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL} , V_{OH}

Description

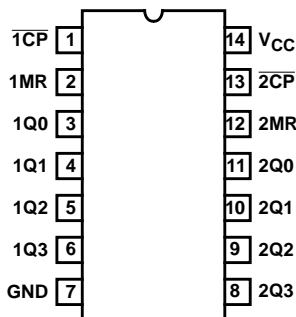
The Harris CD74HC393 and CD74HCT393 are 4-stage ripple-carry binary counters. All counter stages are master-slave flip-flops. The state of the stage advances one count on the negative transition of each clock pulse; a high voltage level on the MR line resets all counters to their zero state. All inputs and outputs are buffered.

Ordering Information

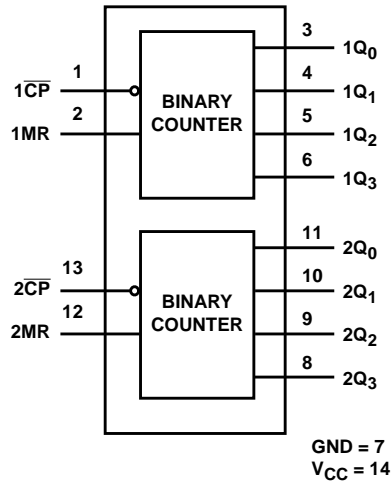
PART NUMBER	TEMP. RANGE ($^\circ C$)	PACKAGE	PKG. NO.
CD74HC393E	-55 to 125	14 Ld PDIP	E14.3
CD74HCT393E	-55 to 125	14 Ld PDIP	E14.3

Pinout

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(PDIP, SOIC)
TOP VIEW



Functional Diagram



TRUTH TABLE

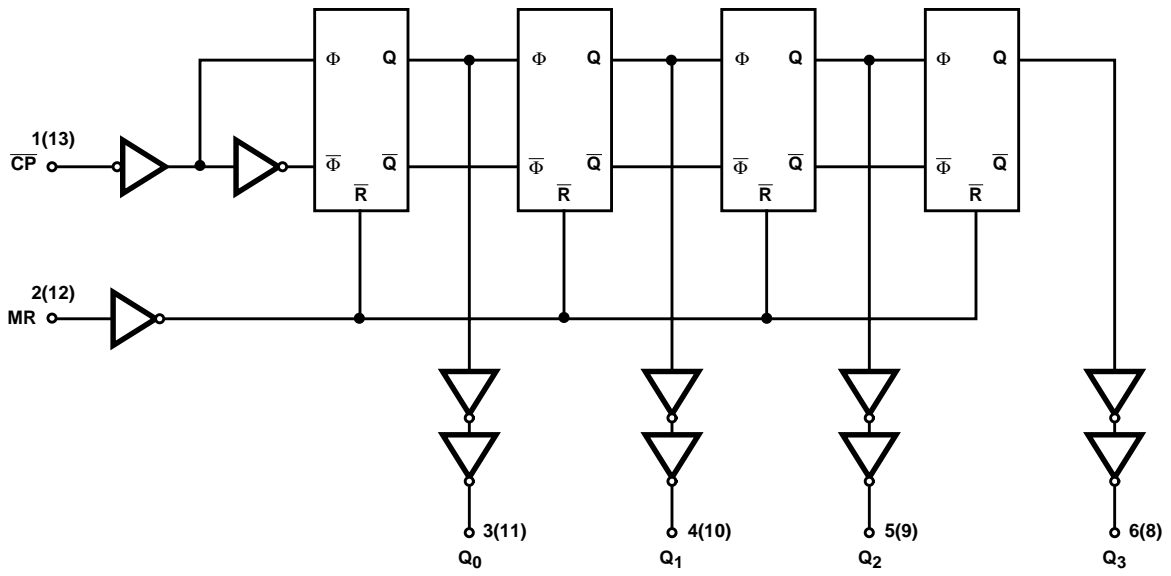
CP COUNT	OUTPUTS			
	Q ₀	Q ₁	Q ₂	Q ₃
0	L	L	L	L
1	H	L	L	L
2	L	H	L	L
3	H	H	L	L
4	L	L	H	L
5	H	L	H	L
6	L	H	H	L
7	H	H	H	L
8	L	L	L	H
9	H	L	L	H
10	L	H	L	H
11	H	H	L	H
12	L	L	H	H
13	H	L	H	H
14	L	H	H	H
15	H	H	H	H

CP COUNT	MR	OUTPUT
↑	L	No Change
↓	L	Count
X	H	L L L L

NOTE: H = High Voltage Level, L = Low Voltage Level, X = Don't Care,
 ↑ = Transition from Low to High Level, ↓ = Transition from High to Low.

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Logic Diagram



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Absolute Maximum Ratings

DC Supply Voltage, V_{CC}	-0.5V to 7V
DC Input Diode Current, I_{IK}	
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$	$\pm 20mA$
DC Output Diode Current, I_{OK}	
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$	$\pm 20mA$
DC Output Source or Sink Current per Output Pin, I_O	
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$	$\pm 25mA$
DC V_{CC} or Ground Current, I_{CC} or I_{GND}	$\pm 50mA$

Thermal Information

Thermal Resistance (Typical, Note 3)	θ_{JA} (°C/W)
PDIP Package	90
SOIC Package	175
Maximum Junction Temperature	150°C
Maximum Storage Temperature Range	-65°C to 150°C
Maximum Lead Temperature (Soldering 10s)	300°C
(SOIC - Lead Tips Only)	

Operating Conditions

Temperature Range (T_A)	-55°C to 125°C
Supply Voltage Range, V_{CC}	
HC Types2V to 6V
HCT Types4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O	0V to V_{CC}
Input Rise and Fall Time	
2V	1000ns (Max)
4.5V	500ns (Max)
6V	400ns (Max)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads	V_{OH}	V_{IH} or V_{IL}	-	-	-	-	-	-	-	-	-	V
			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
			-5.2	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads	V_{OL}	V_{IH} or V_{IL}	-	-	-	-	-	-	-	-	-	V
			4	4.5	-	-	0.26	-	0.33	-	0.4	V
			5.2	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	± 0.1	-	± 1	-	± 1	μA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	μA

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DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V _I (V)	I _O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HCT TYPES												
High Level Input Voltage	V _{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V _{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I _I	V _{CC} and GND	0	5.5	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	I _{CC}	V _{CC} or GND	0	5.5	-	-	8	-	80	-	160	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI _{CC}	V _{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA

NOTE: For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
nCP	0.4
nMR	1

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Table, e.g., 360μA max at 25°C.

Prerequisite for Switching Specifications

PARAMETER	SYMBOL	V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES										
Maximum Clock Frequency	f _{MAX}	2	6	-	-	5	-	4	-	ns
		4.5	30	-	-	24	-	20	-	ns
		6	35	-	-	28	-	24	-	ns
Clock Pulse Width	t _W	2	80	-	-	100	-	120	-	ns
		4.5	16	-	-	20	-	24	-	ns
		6	14	-	-	17	-	20	-	ns
Reset Recovery Time	t _{REC}	2	5	-	-	5	-	5	-	ns
		4.5	5	-	-	5	-	5	-	ns
		6	5	-	-	5	-	5	-	ns

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Prerequisite for Switching Specifications (Continued)

PARAMETER	SYMBOL	V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Reset Pulse Width	t _W	2	80	-	-	100	-	120	-	ns
		4.5	16	-	-	20	-	24	-	ns
		6	14	-	-	17	-	20	-	ns
HCT TYPES										
Maximum Clock Frequency	f _{MAX}	4.5	27	-	-	22	-	18	-	MHz
Clock Pulse Width	t _W	4.5	19	-	-	24	-	29	-	ns
Reset Recovery Time	t _{REC}	4.5	5	-	-	5	-	5	-	ns
Reset Pulse Width	t _W	4.5	16	-	-	20	-	24	-	ns

Switching Specifications Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay Time (Figure 1) Q _n to Q _{n+1}	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	-	45	-	55	-	70	ns
			4.5	-	-	9	-	11	-	14	ns
		C _L = 15pF	5	-	4	-	-	-	-	-	ns
		C _L = 50pF	6	-	-	8	-	9	-	12	ns
nCP to nQ ₀	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	59	ns
		C _L = 15pF	5	-	12	-	-	-	-	-	ns
		C _L = 50pF	6	-	-	26	-	33	-	50	ns
nCP to nQ ₁	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	-	190	-	245	-	295	ns
			4.5	-	-	38	-	49	-	59	ns
			6	-	-	33	-	42	-	50	ns
nCP to nQ ₂	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	-	240	-	300	-	360	ns
			4.5	-	-	48	-	60	-	72	ns
			6	-	-	41	-	51	-	61	ns
nCP to nQ ₃	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	-	285	-	355	-	430	ns
			4.5	-	-	57	-	71	-	86	ns
			6	-	-	48	-	60	-	73	ns
MR to Q _n	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	-	135	-	170	-	205	ns
			4.5	-	-	27	-	34	-	41	ns
		C _L = 15pF	5	-	11	-	-	-	-	-	ns
		C _L = 50pF	6	-	-	23	-	29	-	35	ns
Output Transition Time (Figure 1)	t _{TLH} , t _{THL}	C _L = 50pF	2	-	-	75	-	95	-	110	ns
			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	16	-	19	ns
Input Capacitance	C _{IN}	C _L = 50pF	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 4, 5)	C _{PD}	C _L = 15pF	5	-	20	-	-	-	-	-	pF

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Switching Specifications Input $t_r, t_f = 6\text{ns}$ (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HCT TYPES											
Propagation Delay Time (Figure 1) Q_n to Q_{n+1}	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	4.5	-	-	12	-	15	-	18	ns
		$C_L = 15\text{pF}$	5	-	4	-	-	-	-	-	ns
\overline{nCP} to nQ_0	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	4.5	-	-	32	-	40	-	48	ns
		$C_L = 15\text{pF}$	5	-	13	-	-	-	-	-	ns
\overline{nCP} to nQ_1	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	4.5	-	-	44	-	55	-	66	ns
\overline{nCP} to nQ_2	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	4.5	-	-	50	-	63	-	75	ns
\overline{nCP} to nQ_3	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	4.5	-	-	62	-	78	-	93	ns
MR to Q_n	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	4.5	-	-	32	-	40	-	48	ns
		$C_L = 15\text{pF}$	5	-	13	-	-	-	-	-	ns
Output Transition	t_{TLH}, t_{THL}	$C_L = 50\text{pF}$	4.5	-	-	15	-	19	-	22	ns
Input Capacitance	C_{IN}	$C_L = 15\text{pF}$	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 4, 5)	C_{PD}	$C_L = 15\text{pF}$	5	-	21	-	-	-	-	-	pF

NOTES:

- C_{PD} is used to determine the dynamic power consumption, per stage.
- $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms

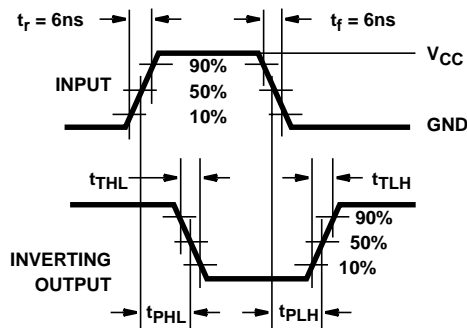


FIGURE 1. HC AND HCU TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

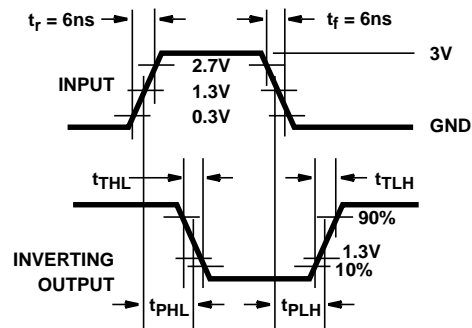


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

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